

REMARKS

Claims 1-61 were originally submitted in the parent application. Method claims 42-61 were subject to restriction in the parent and are now submitted in this divisional application along with new dependent claims 62-84. Accordingly, claims 42-84 are now pending. Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "Version with Markings to Show Changes Made".

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

43. (Amended) The method of claim 42 wherein the act of oxidizing the porous silicon layer to form a layer of porous silicon dioxide comprises oxidizing the porous silicon layer to form a layer of porous silicon dioxide having a relative dielectric constant of less than [three] 3.

56. (Amended) A method of fabricating a field emission display baseplate comprising:

forming conductors on a substrate;

forming a [layer of] porous silicon dioxide layer on the conductors and on the substrate[;], the porous silicon dioxide layer comprising columnar spacers of silicon dioxide with pores between the columnar spacers;

forming an extraction grid on the porous silicon dioxide layer;

etching openings through the silicon dioxide and the extraction grid; and

forming emitters in the openings in the porous silicon dioxide and the extraction grid.

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